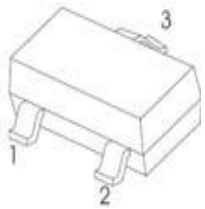
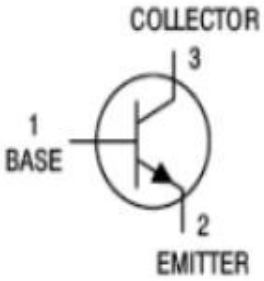
TRANSI STOR (NPN)	SOT-23 Plastic-Encapsulate Transistors

SOT-23





1.BASE
2.EMITTER
3.COLLECTOR

Marking :1D

Features

※ Complimentary to MMBTA92

※ Collector Current: Ic=0.5A

※ High breakdown voltage

※ Low collector-emitter saturation voltage

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	300	V
Collector-Emitter Voltage	VCEO	300	V
Emitter-Base Voltage	VEBO	6	V
Collector Current	IC	500	mA
Collector Power Dissipation	PC	350	mW
Thermal Resistance From Junction To Ambient	RΘJA	416	℃/W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃

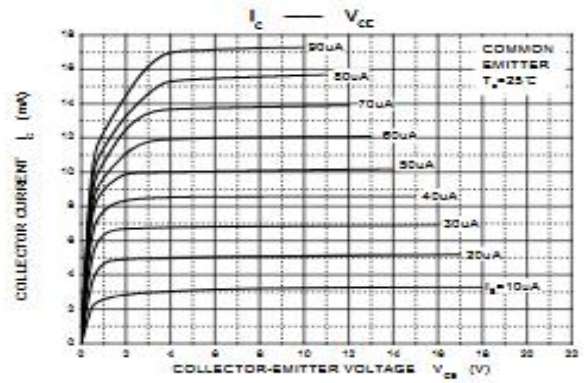
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

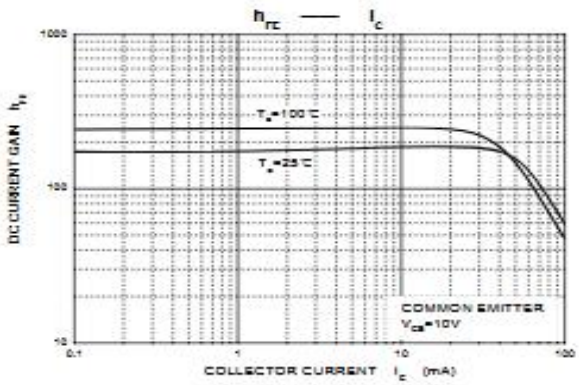
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	300		500	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	300		500	V
Emitter-base breakdown voltage	V(BR)EBO	IE= 100μA, IC=0	6		30	V
Collector cut-off current	ICBO	VCB= 300 V , IE=0			0.8	μA
Collector cut-off current	ICEO	VCE= 300V , IE=0			0.8	μA
Emitter cut-off current	IEBO	VEB= 6V , IC=0			1	μA
DC current gain	hFE	VCE= 10V, IC= 1mA	60			
	hFE	VCE= 10V, IC= 10mA	100		200	
	hFE	VCE= 10V, IC= 30mA	60			
Collector-emitter saturation voltage	VCE(sat)	IC= 30 mA, IB= 3mA			0.2	V
Base-emitter saturation voltage	VBE(sat)	IC= 30 mA, IB= 3mA			1.2	V
Transition frequency	fT	VCE=20V, IC= 20mA f=30MHz	50		300	MHz
Collector Current Capacitance	Cod	VCB= 10V, IE=0, f=1MHz			10	pF

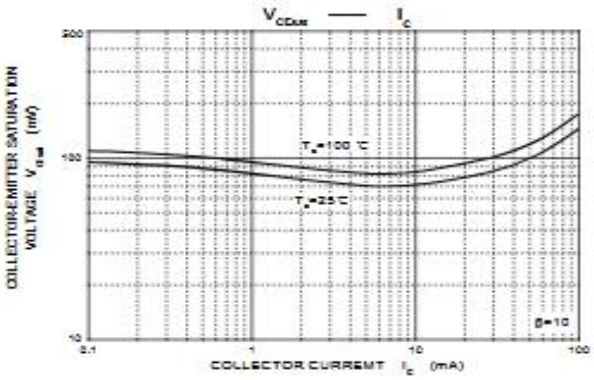
CLASSIFICATION OF hFE

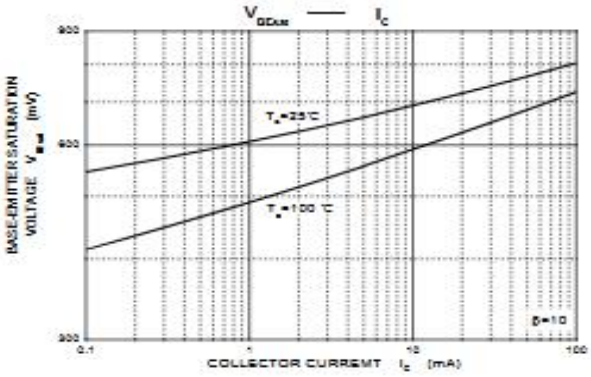
Rank	**L**	
Range	**100-200**	
MARKING	**1D**	

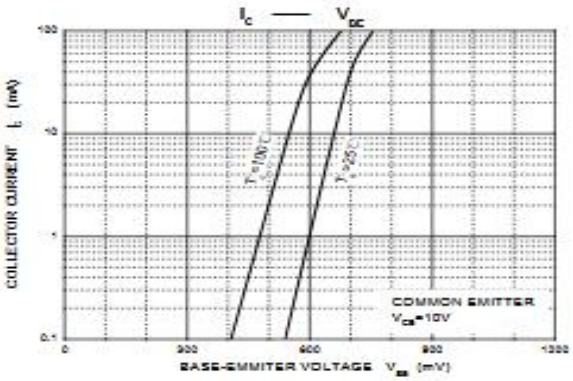
TYPICAL ELEC TRICAL AND THERMAL CHARACTERISTICS

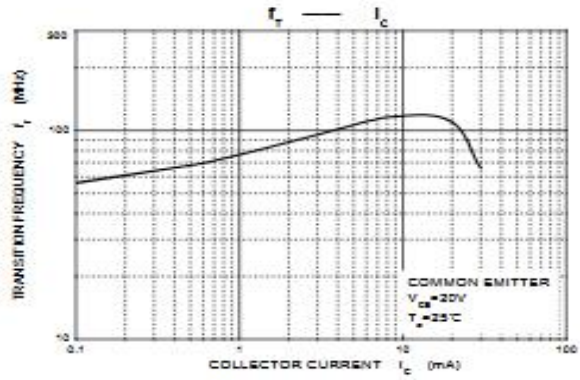


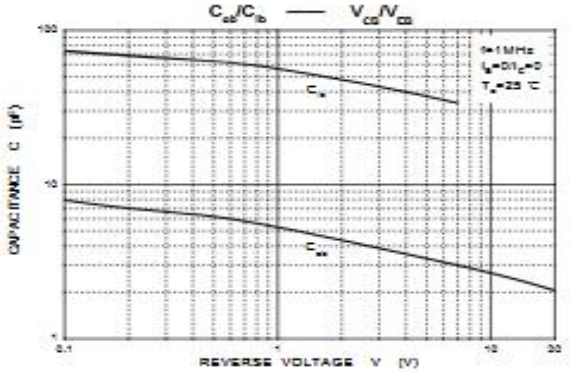


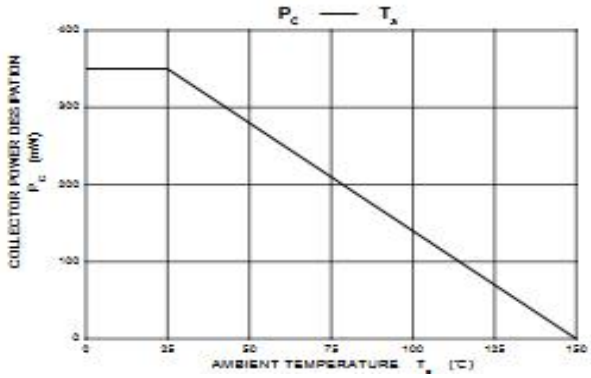












单击下面可查看定价，库存，交付和生命周期等信息

>>DIOS(迪恩思)